

Amendments to the Claims

Claim 1 (Canceled).

2. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the gaseous first precursor comprises an amido metal organic.

3. (Original): The method of claim 2 wherein the amido metal organic is a tetrakis amido metal compound.

4. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the gaseous first precursor comprises an imido metal organic.

5. (Previously Presented): The method of claim 17 wherein the second precursor plasma comprises hydrogen.

6. (Original): The method of claim 5 wherein the second precursor plasma comprises at least one of SiH₄, Si₂H₆, BH₃, and B₂H₆.

7. (Original): The method of claim 5 wherein the second precursor plasma comprises H₂.

8. (Original): The method of claim 5 wherein the second precursor plasma consists essentially of H₂.

Claim 9 (Canceled).

10. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the second precursor plasma is void of nitrogen.

11. (Previously Presented): The method of claim 17 wherein the second precursor plasma comprises NH₃.

12. (Previously Presented): The method of claim 17 wherein the second precursor plasma consists essentially of NH₃.

Claim 13 (Canceled).

14. (Previously Presented): The method of claim 17 wherein the first precursor consists essentially of tetrakisdimethylamido hafnium, the second precursor plasma consists essentially of H₂, and the conductive metal nitride comprises hafnium nitride.

15. (Previously Presented): The method of claim 17 wherein the first precursor consists essentially of tetrakisdimethylamido titanium, the second precursor plasma consists essentially of NH₃, and the conductive metal nitride comprises TiN.

16. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the chemisorbing ~~with the~~ of the first species is void of plasma.

17. (Currently Amended): An atomic layer deposition method of forming a conductive metal nitride-comprising layer in the fabrication of integrated circuitry, comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate from a gaseous first precursor comprising at least one of an amido metal organic compound or an imido metal organic compound, the first species monolayer comprising organic groups;

contacting the chemisorbed first species with a second precursor plasma effective to react with the first species monolayer to remove organic groups from the first species monolayer; the chemisorbing with the of the first species being void of plasma, and further comprising feeding both of the first precursor and the second precursor to the chamber in the absence of plasma during the chemisorbing; and

successively repeating said chemisorbing and contacting under conditions effective to form a layer of material on the substrate comprising a conductive metal nitride.

Claims 18-21 (Canceled).

22. (Currently Amended): The method of claim 1 claim 26 wherein the second precursor plasma is generated from applying plasma power to a flowing second precursor externally of the deposition chamber.

23. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the metal of the metal nitride is selected from the group consisting of any of metal groups 3, 4, 5, 6, 7, the lanthanide series and the actinide series of the periodic table, and mixtures thereof.

24. (Currently Amended): The method of ~~claim 1~~ claim 26 comprising a period of time intermediate said chemisorbing and contacting wherein no gas is flowed to the deposition chamber.

25. (Original): The method of claim 24 wherein the second precursor plasma is generated from feeding the second precursor to the deposition chamber with plasma power being applied thereto within the deposition chamber, said plasma power being started prior to feeding the second precursor to the deposition chamber during said period of time and continued while feeding the second precursor to the deposition chamber.

26. (Previously Presented): An atomic layer deposition method of forming a conductive metal nitride-comprising layer in the fabrication of integrated circuitry, comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate from a gaseous first precursor comprising at least one of an amido metal organic compound or an imido metal organic compound, the first species monolayer comprising organic groups;

contacting the chemisorbed first species with a second precursor plasma effective to react with the first species monolayer to remove organic groups from the first species monolayer, pressure within the chamber during the chemisorbing being lower than during the contacting; and

successively repeating said chemisorbing and contacting under conditions effective to form a layer of material on the substrate comprising a conductive metal nitride.

27. (Previously Presented): The method of claim 26 wherein pressure within the chamber during the chemisorbing is at least five times lower than during the contacting.

28. (Previously Presented): The method of claim 26 wherein pressure within the chamber during the chemisorbing is at least ten times lower than during the contacting.

Claim 29 (Canceled).

30. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the conductive metal nitride comprises carbon.

31. (Original): The method of claim 30 wherein carbon is present in the conductive metal nitride at an atomic ratio of carbon atoms to metal atoms of no greater than 1:3.

32. (Original): The method of claim 31 wherein metal atoms are present in the conductive metal nitride at an atomic ratio of metal atoms to nitrogen atoms at greater than 1:1.

33. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the layer of material has a resistivity of no greater than 5×10^3 microohm·cm.

34. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the layer of material has a resistivity of no greater than 2×10^3 microohm·cm.

35. (Currently Amended): The method of ~~claim 1~~ claim 26 wherein the layer of material has a resistivity of less than 1×10^3 microohm·cm.

36. (Previously Presented): An atomic layer deposition method of forming a conductive metal nitride-comprising layer in the fabrication of integrated circuitry, comprising:

providing a substrate within a deposition chamber;

in the absence of plasma, chemisorbing a first species to form a first species monolayer onto the substrate from a gaseous first precursor comprising at least one of an amido metal organic compound or an imido metal organic compound, the first species monolayer comprising organic groups;

contacting the chemisorbed first species with a second precursor plasma effective to react with the first species monolayer to remove organic groups from the first species monolayer; the second precursor plasma being generated from feeding the second precursor to the deposition chamber with plasma power being applied to the second precursor within the deposition chamber; said plasma power being started prior to feeding the second precursor to the deposition chamber, continued while feeding the second precursor to the deposition chamber, and continued after stopping feeding of the second precursor to the deposition chamber; and

ceasing said plasma power at some point after stopping feeding of the second precursor, and then successively repeating said chemisorbing, contacting and ceasing under conditions effective to form a layer of material on the substrate comprising a conductive metal nitride.

37. (Original): The method of claim 36 wherein the gaseous first precursor comprises an amido metal organic.

38. (Original): The method of claim 37 wherein the amido metal organic is a tetrakis amido metal compound.

39. (Original): The method of claim 36 wherein the gaseous first precursor comprises an imido metal organic.

40. (Original): The method of claim 36 wherein the second precursor plasma comprises hydrogen.

41. (Original): The method of claim 40 wherein the second precursor plasma comprises at least one of SiH₄, Si₂H₆, BH₃, and B₂H₆.

42. (Original): The method of claim 40 wherein the second precursor plasma comprises H₂.

43. (Original): The method of claim 40 wherein the second precursor plasma consists essentially of H₂.

44. (Original): The method of claim 36 wherein the second precursor plasma is void of hydrogen.

45. (Original): The method of claim 36 wherein the second precursor plasma is void of nitrogen.

46. (Original): The method of claim 36 wherein the second precursor plasma comprises NH₃.

47. (Original): The method of claim 36 wherein the second precursor plasma consists essentially of NH₃.

48. (Original): The method of claim 36 wherein the second precursor plasma comprises CO.

49. (Original): The method of claim 36 wherein the first precursor consists essentially of tetrakisdimethylamido hafnium, the second precursor plasma consists essentially of H₂, and the conductive metal nitride comprises hafnium nitride.

50. (Original): The method of claim 36 wherein the first precursor consists essentially of tetrakisdimethylamido titanium, the second precursor plasma consists essentially of NH₃, and the conductive metal nitride comprises TiN.

51. (Original): The method of claim 36 further comprising feeding the second precursor to the chamber in the absence of plasma during the chemisorbing.

52. (Original): The method of claim 36 wherein the metal of the metal nitride is selected from the group consisting of any of metal groups 3, 4, 5, 6, 7, the lanthanide series and the actinide series of the periodic table, and mixtures thereof.

53. (Original): The method of claim 36 comprising a period of time intermediate said chemisorbing and contacting wherein no gas is flowed to the deposition chamber.

54. (Original): The method of claim 53 wherein said plasma power is started during said period of time.

55. (Original): The method of claim 36 wherein pressure within the chamber during the chemisorbing is lower than during the contacting.

56. (Original): The method of claim 36 wherein pressure within the chamber during the chemisorbing is at least five times lower than during the contacting.

57. (Original): The method of claim 36 wherein pressure within the chamber during the chemisorbing is at least ten times lower than during the contacting.

58. (Original): The method of claim 36 wherein metal atoms are present in the conductive metal nitride at an atomic ratio of metal atoms to nitrogen atoms at greater than 1:1.

59. (Original): The method of claim 36 wherein the conductive metal nitride comprises carbon.

60. (Original): The method of claim 59 wherein carbon is present in the conductive metal nitride at an atomic ratio of carbon atoms to metal atoms of no greater than 1:3.

61. (Original): The method of claim 60 wherein metal atoms are present in the conductive metal nitride at an atomic ratio of metal atoms to nitrogen atoms at greater than 1:1.

62. (Original): The method of claim 36 wherein the layer of material has a resistivity of no greater than 5×10^3 microohm·cm.

63. (Original): The method of claim 36 wherein the layer of material has a resistivity of no greater than 2×10^3 microohm·cm.

64. (Original): The method of claim 36 wherein the layer of material has a resistivity of less than 1×10^3 microohm·cm.

65. (Previously Presented): The method of claim 17 wherein the second precursor plasma comprises at least one of BH₃ and B₂H₆.

66. (Previously Presented): The method of claim 17 wherein the first precursor comprises a combination of metal organic compounds containing different metals..

67. (Previously Presented): The method of claim 17 wherein the chemisorbing comprises flowing the first precursor to the substrate within the chamber through a showerhead, the second precursor being fed to the substrate during the contacting in a manner which bypasses the showerhead.

68. (Previously Presented): The method of claim 17 wherein the successively repeating leaves oxygen present at an outermost surface of said layer.